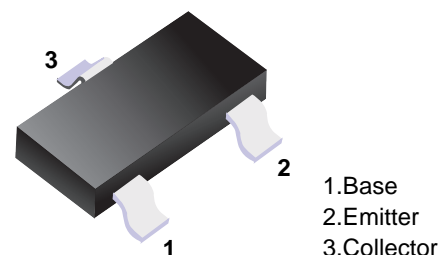


PNP Transistors



■ Simplified outline(SOT-23)

■ Features

- High voltage and high current
- High hFE: hFE = 70~400
- Low noise: NF = 1dB (typ.), 10dB (max)
- Complementary to 2SC2712

■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-50	V
Collector - Emitter Voltage	V _{CE0}	-50	
Emitter - Base Voltage	V _{EB0}	-5	
Collector Current - Continuous	I _c	-150	mA
Base Current	I _B	-30	
Collector Power Dissipation	P _c	150	mW
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{stg}	-55 to 125	

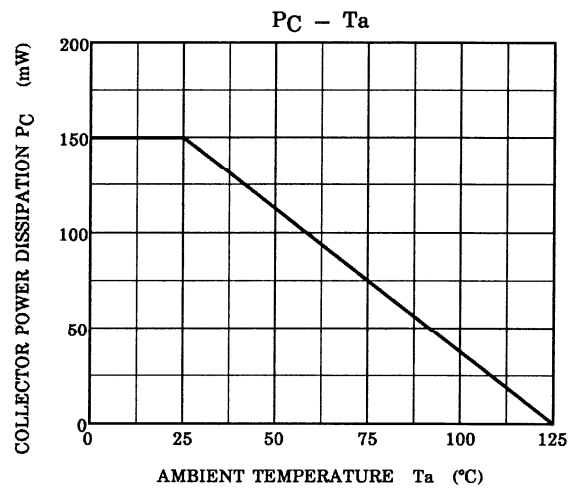
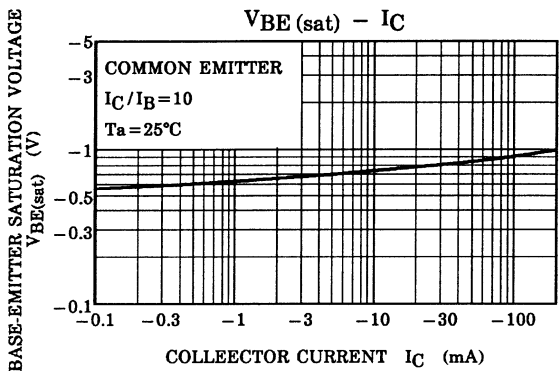
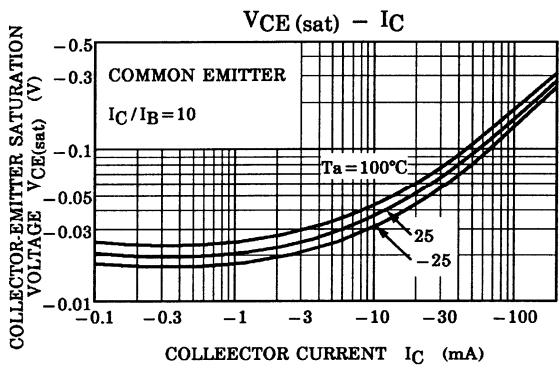
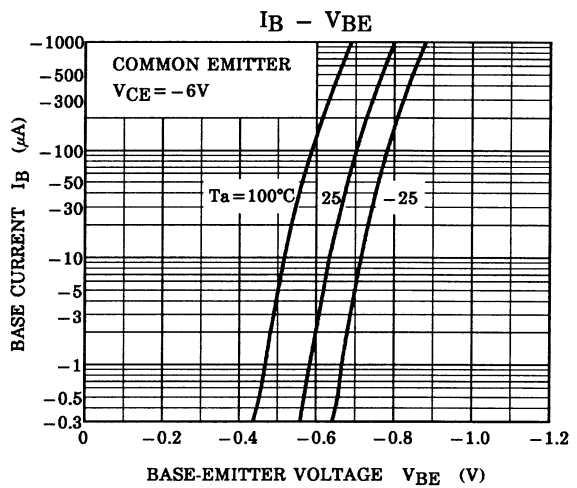
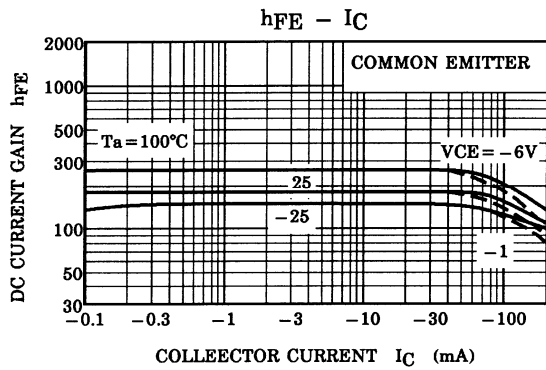
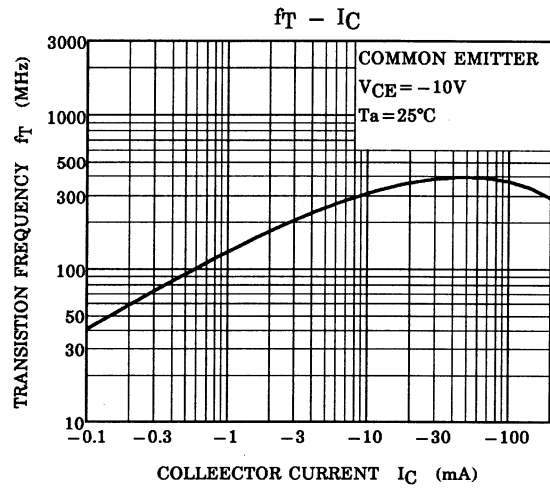
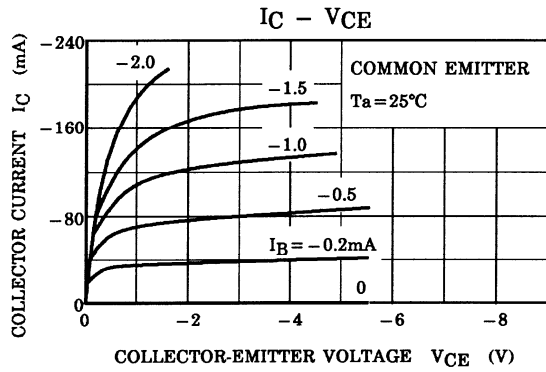
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-50			V
Collector- emitter breakdown voltage	V _{CE0}	I _c = -1 mA, I _B =0	-50			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _c =0	-5			
Collector-base cut-off current	I _{CB0}	V _{CB} = -50 V, I _E =0			-100	nA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _c =0			-100	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-100 mA, I _B =-10mA			-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =-100 mA, I _B =-10mA			-1.2	
DC current gain	h _{FE}	V _{CE} = -6V, I _c = -2mA	70		400	
Noise figure	NF	V _{CE} = -6 V, I _C = -0.1 mA, f = 1 kHz, R _g = 10 kΩ,			10	dB
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0,f=1MHz			7	pF
Transition frequency	f _T	V _{CE} = -10V, I _c = -1mA	80			MHz

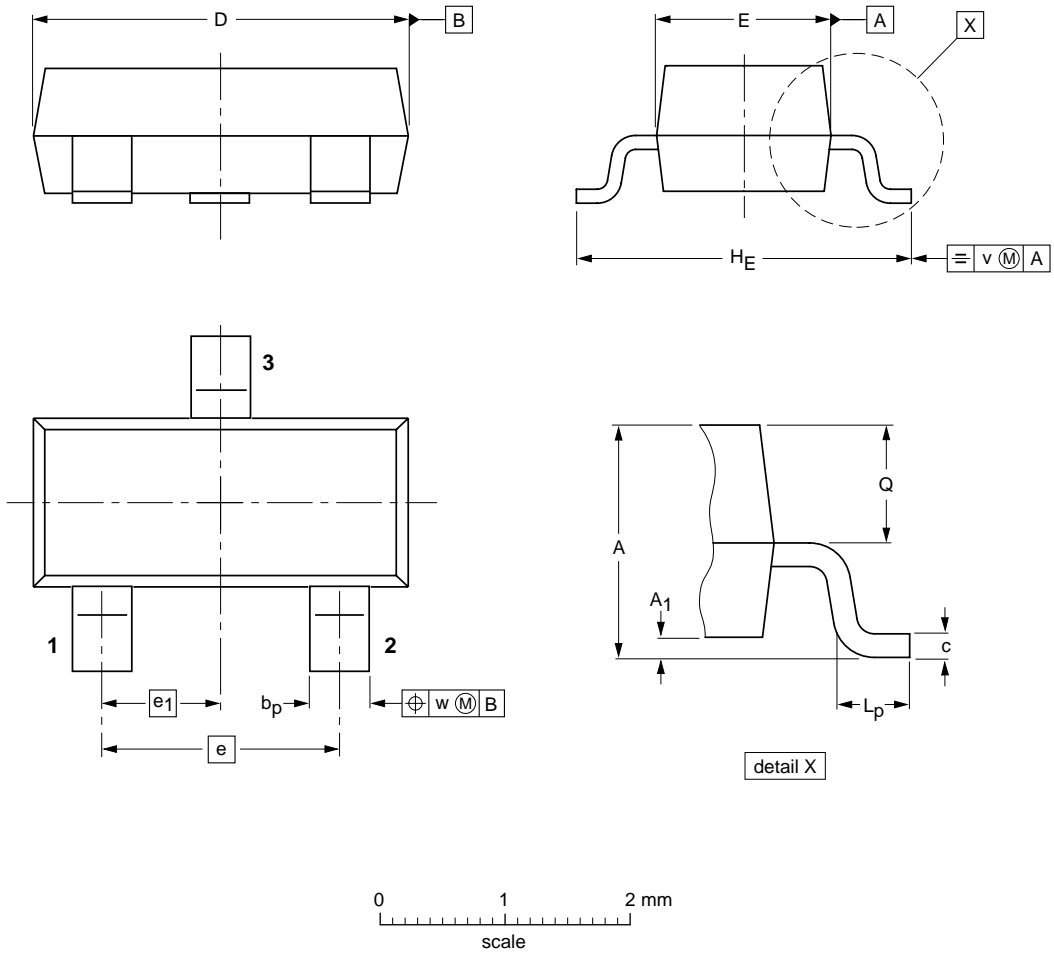
■ Classification of hfe

Type	2SA1162-O	2SA1162-Y	2SA1162-G
Range	70-140	120-240	200-400
Marking	SO	SY	SG

■ Typical Characteristics



■ SOT-23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1